

Application No.: 09/161,520
(80001-1450)

Docket No.: SON-1450/DIV

AMENDMENTS TO THE CLAIMS

Please cancel claims 12, 13, and 16-19 and amend claims 14, 20, and 24-27 as set forth below.

Claims 1-14 are CANCELED.

14. (CURRENTLY AMENDED) A chemical-mechanical polishing process ~~according to claim 13, for planarizing one or more thin films formed on a substrate, wherein the chemical-mechanical polishing is performed using an abrasive particles basic slurry in which all of said abrasive particles consist of boehmite, wherein the particles of boehmite are formed by dipping particles of Al in hot water, and wherein said hot water~~ sodium aluminate is added with sodium aluminato said hot water.

Claims 16-19 are CANCELED.

20. (CURRENTLY AMENDED) A chemical-mechanical polishing process ~~according to claim 19 for planarizing one or more films formed on a substrate, wherein said thin films are subjected to chemical-mechanical polishing using an abrasive particles slurry in which all of said abrasive particles consist essentially of boehmite, wherein residual slurry and contamination are removed by spin cleaning, wherein the abrasive particles of boehmite are formed by dipping particles of Al in hot water, and wherein said hot water~~ sodium aluminate is added with sodium aluminato said hot water.

21. (CANCELED)

22. (PREVIOUSLY PRESENTED) A polishing process which comprises the steps of:

forming abrasive boehmite particles by dipping particles of aluminum in heated water with sodium aluminate added thereto;

creating a slurry containing said abrasive boehmite particles; and

planarizing at least one film formed on a substrate by employing a chemical-mechanical polishing process using said slurry.

23. (CANCELED)

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24. (CURRENTLY AMENDED) ~~A-~~The polishing process according to claim 22, wherein said heated water is about 80 °C.

25. (CURRENTLY AMENDED) ~~A-~~The polishing process according to claim 22, wherein said slurry used in said chemical-mechanical polishing process is a basic slurry.

26. (CURRENTLY AMENDED) ~~A-~~The polishing process according to claim 25, wherein said step of creating a slurry comprises suspending said boehmite particles in a solution containing KOH, water, and an alcohol.

27. (CURRENTLY AMENDED) ~~A-~~The polishing process according to claim 22, wherein said film is an interlayer dielectric film.